

**Amendments to the Claims**

1. (*Currently Amended*) A composite substrate comprising  
\_\_\_\_\_ a carrier composed of a carrier material,  
\_\_\_\_\_ a first layer composed of a first material, and  
\_\_\_\_\_ an intermediate layer composed of a second material being located between the carrier and the first layer, wherein the first material has a dilatation behavior being substantially the same as that of the carrier material, and having a dilatation mismatch with the second material, the intermediate layer having structures of second material for absorbing stress originating from the dilatation mismatch.
2. (*Original*) A composite substrate according to claim 1, wherein the intermediate layer has a thickness, and the structures extend through the thickness of the intermediate layer.
3. (*Original*) A composite substrate according to claim 1, wherein the structures further extend into the carrier.
4. (*Original*) A composite substrate according to claim 1, wherein the carrier material is the same as the first material.
5. (*Currently Amended*) A composite substrate ~~according to any of the previous claims,~~ according to claim 1, wherein the carrier material and the first material are semiconductors.
6. (*Currently Amended*) A composite substrate ~~according to any of the previous claims,~~ according to claim 1, wherein the second material is an electrically insulating material.
7. (*Currently Amended*) A composite substrate ~~according to any of the previous claims,~~ according to claim 1, the intermediate layer lying in a plane, wherein the dimensions of the structures in the plane of the intermediate layer are less than a centimeter.

8. *(Currently Amended)* A composite substrate ~~according to any of the previous claims,~~ according to claim 1, wherein the carrier lies in a plane and wherein the structures have a line-symmetric shape in a cross-section perpendicular to the plane of the carrier.

9. *(Currently Amended)* A composite substrate ~~according to any of the previous claims,~~ according to claim 1, wherein the carrier lies in a plane and wherein the structures have a circular, square, rectangular or rhombic shape in a cross-section parallel to the plane of the carrier.

10. *(Currently Amended)* A composite substrate ~~according to any of the previous claims,~~ according to claim 1, wherein the composite substrate is a silicon-on-insulator wafer.

11. *(Original)* A method to relieve stress in a composite substrate, comprising:  
    providing a carrier, composed of a carrier material, with on top thereof an intermediate layer of a second material,  
    forming in the intermediate layer structures which extend through the intermediate layer,  
    bonding on the intermediate layer a first substrate of a first material having a dilatation behavior being substantially the same as that of the carrier material.

12. *(Original)* A method according to claim 11, in which the structures are formed into the carrier.

13. *(Currently Amended)* A method ~~according to claim 11 or 12,~~ according to claim 11, wherein the forming of the structures is executed by integrally patterning the structures over the intermediate layer.

14. *(Currently Amended)* A method ~~according to claim 11 or 12,~~ according to claim 11, wherein the forming of the structures is executed by locally patterning the structures in clusters over the intermediate layer.

15. (*Currently Amended*) A method ~~according to any of claims 11 to 14~~, according to claim 11, wherein the patterning comprises applying millimeter, micrometer or nanometer structural texturing.

16. (*Currently Amended*) A method ~~according to any of claims 11 to 14~~, according to claim 11, wherein the patterning comprises applying imprint lithography.

17. (*Currently Amended*) A method ~~according to any of claims 11 to 16~~, according to claim 11, wherein the intermediate layer lies in a plane, and wherein the forming of the structures is such that the dimensions of the structures in the plane of the intermediate layer are less than a centimeter.

18. (*Currently Amended*) A method ~~according to any of claims 11 to 17~~, according to claim 11, wherein the carrier lies in a plane, and wherein the forming of the structures is such that the structures have a line-symmetric shape in a cross-section perpendicular to the plane of the carrier.

19. (*Currently Amended*) A method ~~according to any of claims 11 to 18~~, according to claim 11, wherein the carrier lies in a plane, and wherein the forming of the structures is such that the structures have a circular, square, rectangular or rhombic shape in a cross-section parallel to the plane of the carrier.

20. (*Currently Amended*) Use of the method ~~of any of claims 11 to 19~~ as recited claim 11, for making a silicon-on-insulator substrate.